## **EAST Search History**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4370	438/758,761,765-770.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 07:51
L2	19	1 and (clean\$3 and oxidizing and nitriding and nitrogen and hydrogen and exposure same air)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 07:51
S1	1	("20020014666").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/02/03 21:06
S2 .	2232	treat\$3 near3 oxide same ("h.sub. 2" hydrogen)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/03 21:09
S3	1414	treat\$3 near2 oxide same ("h.sub. 2" hydrogen)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/03 21:09
S4 .	424	treat\$3 near2 oxide near5 ("h.sub. 2" hydrogen)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/03 21:10
S5	61	S4 and semiconductor	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/03 21:10
S6	84	treat\$3 near2 nitride near5 ("h.sub. 2" hydrogen)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/03 21:27

## **EAST Search History**

S7	42	S6 and insulating	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/03 21:28
S8		(clean\$3 and oxidizing and nitriding and nitrogen and hydrogen and exposure same air).clm.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/03 21:36